Yixin

Product Specification

Silicon NPN Power Transistors 2SC3298 2SC3298A 2SC3298B

DESCRIPTION

·With TO-220Fa package

·Complement to type
2SA1306,2SA1306A,2SA1306B

APPLICATIONS

·Power amplifier applications

·Driver stage amplifier applications

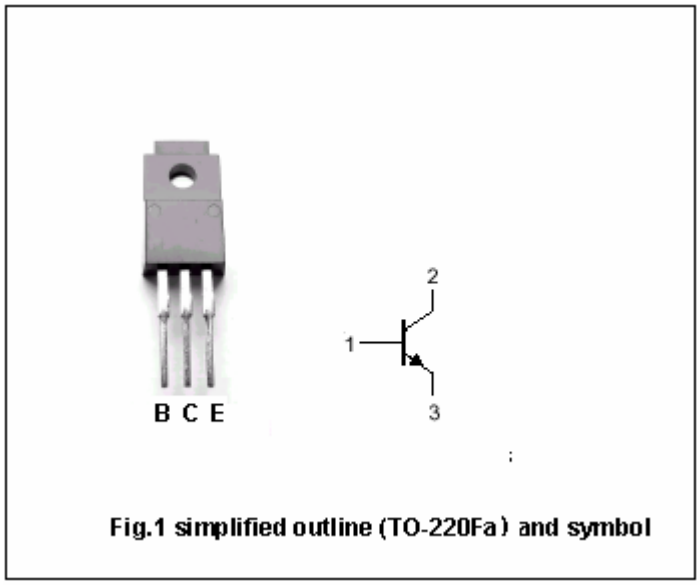

Fig.1 simplified outline (TO-220Fa) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC3298	Open emitter	160	V
		2SC3298A		180	
		2SC3298B		200	
V_{CEO}	Collector-emitter voltage	2SC3298	Open base	160	V
		2SC3298A		180	
		2SC3298B		200	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			1.5	A
I_B	Base current			0.15	A
P_C	Collector power dissipation		T_C=25□	20	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC3298	I_C=10mA , I_B=0	160			V
		2SC3298A		180			
		2SC3298B		200			
V_{CEsat}	Collector-emitter saturation voltage		I_C=0.5A, I_B=50mA			1.5	V
V_{BE}	Base-emitter voltage		I_C=0.5A ,V_{CE}=5V			1.0	V
I_{CBO}	Collector cut-off current		V_{CB}=160V, I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			1.0	μA
h_{FE}	DC current gain		I_C=0.1A ; V_{CE}=5V	70		240	
C_{ob}	Output capacitance		I_E=0 ; V_{CB}=10V,f=1MHz		25		pF
f_T	Transition frequency		I_C=0.1A ; V_{CE}=10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

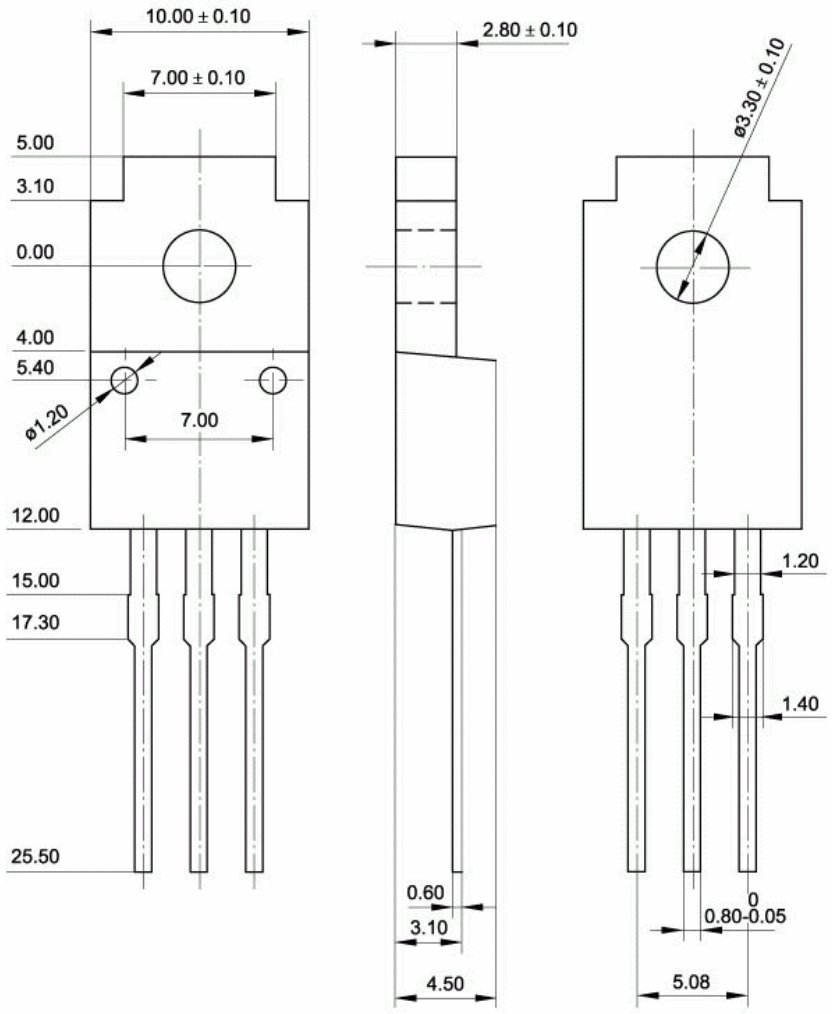

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)